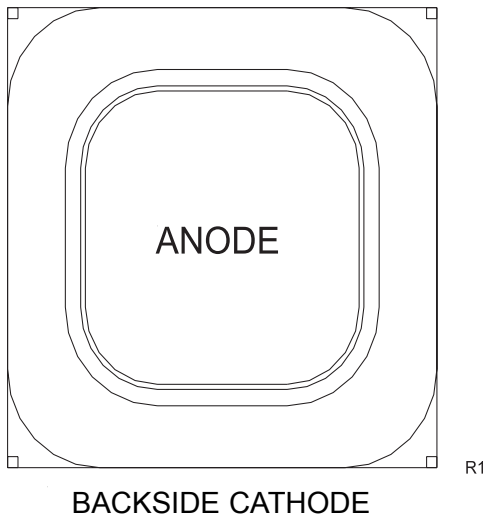


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	14 x 14 MILS
Die Thickness	9.0 MILS
Anode Bonding Pad Area	9.0 x 9.0 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



GROSS DIE PER 4 INCH WAFER

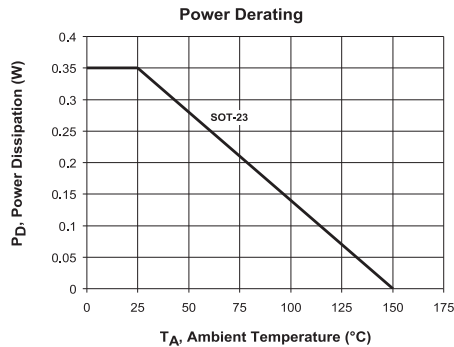
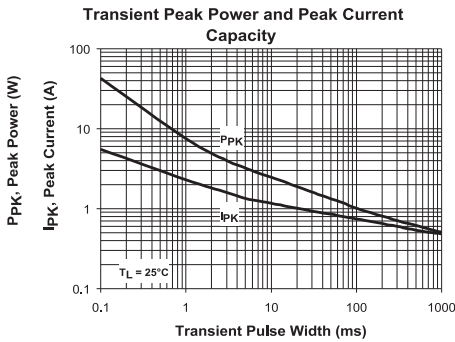
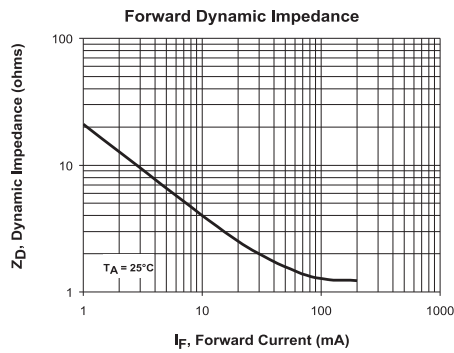
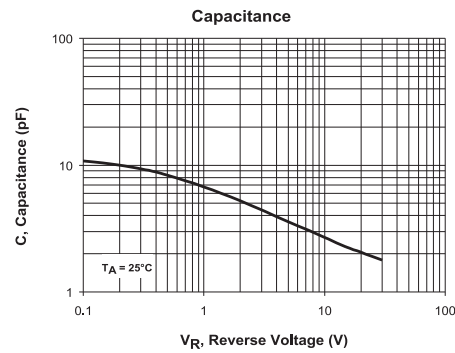
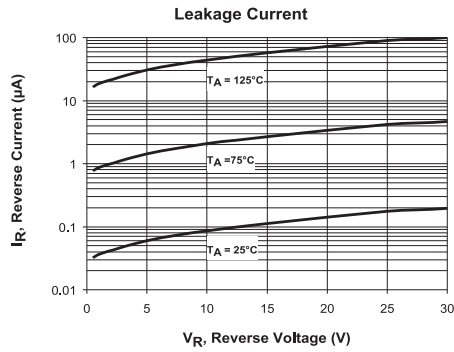
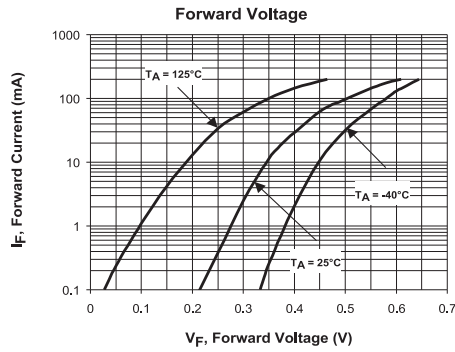
62,250

PRINCIPAL DEVICE TYPES

CMP SH-3
CMP SH-3A
CMP SH-3C
CMP SH-3S

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centalsemi.com

R2 (1-August 2002)



145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centalsemi.com

R2 (1-August 2002)